1.8V Low-Power Open-Drain Output Comparator

Features:

- Propagation Delay at 1.8 V_{DD}: 56 ns (typical) High-to-Low
- Low Quiescent Current: 100 µA (typical)
- Input Offset Voltage: ±3 mV (typical)
- Rail-to-Rail Input: V_{SS} 0.3V to V_{DD} + 0.3V
- Open-Drain Output
- Wide Supply Voltage Range: 1.8V to 5.5V
- Available in Single, Dual and Quad
- Packages: SC70, SOT-23-5, SOIC, MSOP, TSSOP

Typical Applications:

- Laptop Computers
- Mobile Phones
- Hand-held Electronics
- RC Timers
- Alarm and Monitoring Circuits
- Window Comparators
- Multivibrators

Design Aids:

- Microchip Advanced Part Selector (MAPS)
- Analog Demonstration and Evaluation Boards
- Application Notes
- SPICE Macro Model

Related Device:

Push-Pull Output: MCP6561/1R/1U/2/4

Typical Application



Description:

The Microchip MCP6566/6R/6U/7/9 family of opendrain output comparators are offered in single, dual and quad configurations.

These comparators are optimized for low-power 1.8V, single-supply applications with greater than rail-to-rail input operation. The internal input hysteresis eliminates output switching due to internal input noise voltage, reducing current draw.

The open-drain output of the MCP6566/6R/6U/7/9 family requires a pull-up resistor. It supports pull-up voltages that are above and below V_{DD} , which can be used to level shift. The output toggle frequency can reach a typical of 4 MHz (typical) while limiting supply current surges and dynamic power consumption during switching.

This family operates with single supply voltage of 1.8V to 5.5V while drawing less than 100 μ A/comparator of quiescent current (typical).



Package Types

1.0 **ELECTRICAL CHARACTERISTICS**

1.1 Maximum Ratings †

6.5V
V _{SS} + 10.5V
– 0.3V to V _{DD} + 0.3V
- 1.0V to V _{DD} + 1.0V
V _{DD} - V _{SS}
±25 mA
±2 mA
±50 mA
65°C to +150°C
40°C to +125°C
+150°C
≥ 4kV/300V

† Notice: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

†† See Section 4.1.2 "Input Voltage and Current Limits"

Electrical Characteristics: Unless otherwise indicated: V_{DD} = +1.8V to +5.5V, V_{SS} = GND, T_A = +25°C, V_{IN} + = $V_{DD}/2$, V_{IN} = V; and $R_{Pull-Up}$ = 20 k Ω to V_{PU} = V_{DD} (see Figure 1-1).ParametersSymbolMin.Typ.Max.Units in the term of	DC CHARACTERISTICS							
$\begin{tabular}{ c c c c c c } \hline Parameters & Symbol & Min. Typ. Max. Units & Conditions \\ \hline Power Supply \\ \hline Supply Voltage & V_{DD} & 1.8 & & 5.5 & V \\ \hline Supply Voltage & V_{DD} & 1.8 & & 5.5 & V \\ \hline Quiescent Current per comparator & I_Q & 60 & 100 & 130 & \muA & I_{OUT} = 0 \\ \hline Power Supply Rejection Ratio & PSRR & 63 & 70 & & dB & V_{CM} = V_{SS} \\ \hline Power Supply Rejection Ratio & PSRR & 63 & 70 & & dB & V_{CM} = V_{SS} \\ \hline Input \\ \hline Input Offset Voltage & V_{OS} & -10 & \pm 3 & \pm 10 & mV & V_{CM} = V_{SS} (Note 1) \\ \hline Input Offset Drift & \Delta V_{OS} / \Delta T & & \pm 2 & & \mu V/^{\circ}C & V_{CM} = V_{SS} \\ \hline Input Offset Current & I_{OS} & & \pm 1 & & pA & V_{CM} = V_{SS} \\ \hline Input Bias Current & I_{OS} & & \pm 1 & & pA & T_A = \pm 25^{\circ}C, V_{IN^-} = V_{DD}/2 \\ \hline Input Bias Current & I_B & & 11 & & pA & T_A = \pm 25^{\circ}C, V_{IN^-} = V_{DD}/2 \\ \hline Input Hysteresis Voltage & V_{HYST} & 1.0 & & 5.0 & mV \\ \hline Input Hysteresis Linear Temp. Co. & TC_1 & & 10 & & \mu V/^{\circ}C \\ \hline Input Hysteresis Quadratic Temp. Co. & TC_2 & & 0.3 & & \mu V/^{\circ}C \\ \hline Common-Mode Input Voltage Range & V_{CMR} & V_{SS} - 0.2 & & V_{DD} + 0.2 & V & V_{DD} = 1.8V \\ \hline \end{array}$	Electrical Characteristics: Unless oth and $R_{Pull-Up}$ = 20 k Ω to V _{PU} = V _{DD} (see	nerwise indi e <mark>Figure 1-</mark> 1	cated: V _{DD}).) = +1.8V	to +5.5V, V	_{SS} = GNE	0, $T_A = +25^{\circ}C$, $V_{IN} + = V_{DD}/2$, $V_{IN} = V_{SS}$,	
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	Parameters	Symbol	Min.	Тур.	Max.	Units	Conditions	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Power Supply							
$ \begin{array}{ c c c c c c c } \hline Quiescent Current per comparator & I_Q & 60 & 100 & 130 & \mu A & I_{OUT} = 0 \\ \hline Power Supply Rejection Ratio & PSRR & 63 & 70 & - & dB & V_{CM} = V_{SS} \\ \hline Input \\ \hline Input Offset Voltage & V_{OS} & -10 & \pm 3 & +10 & mV & V_{CM} = V_{SS} (Note 1) \\ \hline Input Offset Drift & \Delta V_{OS} / \Delta T & - & \pm 2 & - & \mu V /^{\circ}C & V_{CM} = V_{SS} \\ \hline Input Offset Drift & I_{OS} & - & \pm 1 & - & pA & V_{CM} = V_{SS} \\ \hline Input Offset Current & I_{OS} & - & \pm 1 & - & pA & V_{CM} = V_{SS} \\ \hline Input Bias Current & I_B & - & 1 & - & pA & T_A = +25^{\circ}C, V_{IN} = V_{DD}/2 \\ \hline & - & 60 & - & pA & T_A = +85^{\circ}C, V_{IN} = V_{DD}/2 \\ \hline & - & 1500 & 5000 & pA & T_A = +125^{\circ}C, V_{IN} = V_{DD}/2 \\ \hline Input Hysteresis Voltage & V_{HYST} & 1.0 & - & 5.0 & mV & V_{CM} = V_{SS} (Notes 1, 2) \\ \hline Input Hysteresis Quadratic Temp. Co. & TC_1 & - & 10 & - & \mu V /^{\circ}C \\ \hline Common-Mode Input Voltage Range & V_{CMR} & V_{SS} - 0.2 & - & V_{DD} + 0.2 & V & V_{DD} = 1.8V \\ \hline \end{array}$	Supply Voltage	V _{DD}	1.8	—	5.5	V		
$ \begin{array}{ c c c c c c c c } \hline Power Supply Rejection Ratio & PSRR & 63 & 70 & & dB & V_{CM} = V_{SS} \\ \hline \mbox{Input } \\ \hline \mbox{Input Offset Voltage } & V_{OS} & -10 & \pm 3 & \pm 10 & mV & V_{CM} = V_{SS} (Note 1) \\ \hline \mbox{Input Offset Drift } & \Delta V_{OS}/\Delta T & & \pm 2 & & \mu V/^{\circ}C & V_{CM} = V_{SS} \\ \hline \mbox{Input Offset Current } & I_{OS} & & \pm 1 & & pA & V_{CM} = V_{SS} \\ \hline \mbox{Input Bias Current } & I_{B} & & 1 & & pA & T_A = \pm 25^{\circ}C, V_{IN^-} = V_{DD}/2 \\ \hline \mbox{Input Hysteresis Voltage } & V_{HYST} & 1.0 & & 5.0 & mV \\ \hline \mbox{Input Hysteresis Quadratic Temp. Co. } & TC_2 & & 0.3 & & \mu V/^{\circ}C \\ \hline \mbox{Common-Mode Input Voltage Range } & V_{CMR} & V_{SS} - 0.2 & & V_{DD} + 0.2 & V & V_{DD} = 1.8V \\ \hline \end{tabular}$	Quiescent Current per comparator	۱ _Q	60	100	130	μA	I _{OUT} = 0	
	Power Supply Rejection Ratio	PSRR	63	70		dB	V _{CM} = V _{SS}	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Input					•	•	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Input Offset Voltage	V _{OS}	-10	±3	+10	mV	V _{CM} = V _{SS} (Note 1)	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Input Offset Drift	$\Delta V_{OS} / \Delta T$	—	±2	_	µV/°C	V _{CM} = V _{SS}	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Input Offset Current	I _{OS}	—	±1	_	pА	V _{CM} = V _{SS}	
$ \begin{array}{ c c c c c c c c } \hline & - & 60 & - & pA & T_A = +85^{\circ}C, V_{IN^-} = V_{DD}/2 \\ \hline & - & 1500 & 5000 & pA & T_A = +125^{\circ}C, V_{IN^-} = V_{DD}/2 \\ \hline & Input Hysteresis Voltage & V_{HYST} & 1.0 & - & 5.0 & mV & V_{CM} = V_{SS} (Notes 1, 2) \\ \hline & Input Hysteresis Quadratic Temp. Co. & TC_1 & - & 10 & - & \mu V/^{\circ}C & \\ \hline & Input Hysteresis Quadratic Temp. Co. & TC_2 & - & 0.3 & - & \mu V/^{\circ}C^2 \\ \hline & Common-Mode Input Voltage Range & V_{CMR} & V_{SS}-0.2 & - & V_{DD}+0.2 & V & V_{DD} = 1.8V \\ \hline \end{array}$	Input Bias Current	Ι _Β	—	1	_	pА	$T_A = +25^{\circ}C, V_{IN^-} = V_{DD}/2$	
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$			_	60		pА	$T_A = +85^{\circ}C, V_{IN^-} = V_{DD}/2$	
Input Hysteresis Voltage V_{HYST} 1.05.0mV $V_{CM} = V_{SS}$ (Notes 1, 2)Input Hysteresis Linear Temp. Co. TC_1 10 $\mu V/^{\circ}C$ Input Hysteresis Quadratic Temp. Co. TC_2 0.3 $\mu V/^{\circ}C^2$ Common-Mode Input Voltage Range V_{CMR} V_{SS} -0.2 V_{DD} + 0.2V V_{DD} = 1.8V			_	1500	5000	pА	$T_A = +125^{\circ}C, V_{IN^-} = V_{DD}/2$	
Input Hysteresis Linear Temp. Co.TC1—10— $\mu V/^{\circ}C$ Input Hysteresis Quadratic Temp. Co.TC2—0.3— $\mu V/^{\circ}C^2$ Common-Mode Input Voltage Range V_{CMR} V_{SS} -0.2— V_{DD} + 0.2V V_{DD} = 1.8V	Input Hysteresis Voltage	V _{HYST}	1.0	—	5.0	mV	V _{CM} = V _{SS} (Notes 1, 2)	
Input Hysteresis Quadratic Temp. Co.TC2— 0.3 — $\mu V/^{\circ}C^2$ Common-Mode Input Voltage Range V_{CMR} V_{SS} - 0.2 — V_{DD} + 0.2 V V_{DD} = $1.8V$	Input Hysteresis Linear Temp. Co.	TC ₁	—	10	_	µV/°C		
Common-Mode Input Voltage Range V_{CMR} V_{SS} -0.2 — V_{DD} + 0.2 V V_{DD} = 1.8V	Input Hysteresis Quadratic Temp. Co.	TC ₂	—	0.3		µV/°C ²		
	Common-Mode Input Voltage Range	V _{CMR}	V _{SS} -0.2	—	V _{DD} + 0.2	V	V _{DD} = 1.8V	
V_{SS} -0.3 — V_{DD} + 0.3 V V_{DD} = 5.5V			V _{SS} -0.3	—	V _{DD} + 0.3	V	V _{DD} = 5.5V	
Common-Mode Rejection Ratio CMRR 54 66 — dB V_{CM} = -0.3V to V_{DD} +0.3V, V_{DD} = 5.5	Common-Mode Rejection Ratio	CMRR	54	66	_	dB	V_{CM} = -0.3V to V_{DD} +0.3V, V_{DD} = 5.5V	
50 63 — dB $V_{CM} = V_{DD}/2$ to $V_{DD} + 0.3V$, $V_{DD} = 5.8$			50	63		dB	$V_{CM} = V_{DD}/2$ to V_{DD} +0.3V, V_{DD} = 5.5V	
54 65 — dB V_{CM} = -0.3V to V_{DD} /2, V_{DD} = 5.5V			54	65		dB	V_{CM} = -0.3V to $V_{DD}/2$, V_{DD} = 5.5V	
Common Mode Input Impedance Z _{CM} — 10 ¹³ 4 — Ω pF	Common Mode Input Impedance	Z _{CM}	—	10 ¹³ 4	—	Ω pF		
Differential Input Impedance Z_{DIFF} — 10^{13} 2 — Ω pF	Differential Input Impedance	Z _{DIFF}	—	10 ¹³ 2	_	Ω pF		

Note 1: The input offset voltage is the center of the input-referred trip points. The input hysteresis is the difference between the input-referred trip points.

2: V_{HYST} at different temperatures is estimated using V_{HYST} (T_A) = $V_{HYST} \otimes _{+25^{\circ}C} + (T_{A} - 25^{\circ}C) TC_{1} + (T_{A} - 25^{\circ}C)^{2} TC_{2}$.

3: Limit the output current to Absolute Maximum Rating of 50 mA.

4: The pull-up voltage for the open drain output V_{PULL_UP} can be as high as the absolute maximum rating of 10.5V. In this case, I_{OH} leak can be higher than 1 μ A (see Figure 2-30).

DC CHARACTERISTICS (CONTINUED)

Electrical Characteristics: Unless otherwise indicated: V_{DD} = +1.8V to +5.5V, V_{SS} = GND, T_A = +25°C, V_{IN} + = V_{DD} /2, V_{IN^-} = V_{SS} , and $R_{Pull-Up}$ = 20 k Ω to V_{PU} = V_{DD} (see Figure 1-1). Units **Parameters** Symbol Min. Max. Conditions Typ. **Push-Pull Output** Pull-up Voltage V_{PULL_UP} 1.6 5.5 V ____ High-Level Output Voltage V_{PULL_UP} V (see Figure 1-1) (Notes 3, 4) VOH ____ ____ High-Level Output Current Leakage 1 Note 4 ____ μΑ I_{OH_leak} Low-Level Output Voltage V_{OL} 0.6 V I_{OUT} = 3 mA/8 mA @ V_{DD} = 1.8V/5.5V Short Circuit Current (Notes 3) ±30 mΑ Not to exceed Absolute Max. Rating I_{SC} ____ _ **Output Pin Capacitance** 8 pF COUT

Note 1: The input offset voltage is the center of the input-referred trip points. The input hysteresis is the difference between the input-referred trip points.

2: V_{HYST} at different temperatures is estimated using V_{HYST} (T_A) = $V_{HYST} \otimes _{+25^{\circ}C} + (T_{A} - 25^{\circ}C) TC_{1} + (T_{A} - 25^{\circ}C)^{2} TC_{2}$.

3: Limit the output current to Absolute Maximum Rating of 50 mA.

4: The pull-up voltage for the open drain output V_{PULL}_{UP} can be as high as the absolute maximum rating of 10.5V. In this case, I_{OH}_{leak} can be higher than 1 μ A (see Figure 2-30).

AC CHARACTERISTICS

Electrical Characteristics: Unless otherwise indicated,: Unless otherwise indicated,: V_{DD} = +1.8V to +5.5V, V_{SS} = GND, T_A = +25°C, V_{IN+} = $V_{DD}/2$, V_{IN-} = V_{SS} , $R_{Pull-Up}$ = 20 k Ω to V_{PU} = V_{DD} , and C_L = 25 pf (see Figure 1-1).

Parameters	Symbol	Min.	Тур.	Max.	Units	Conditions
Propagation Delay						
High-to-Low,100 mV Overdrive	t _{PHL}	_	56	80	ns	$V_{CM} = V_{DD}/2, V_{DD} = 1.8V$
		_	34	80	ns	$V_{CM} = V_{DD}/2, V_{DD} = 5.5V$
Output						
Fall Time	t _F	_	20	—	ns	
Maximum Toggle Frequency	f _{TG}	_	4	—	MHz	V _{DD} = 5.5V
		_	2	_	MHz	V _{DD} = 1.8V
Input Voltage Noise	E _{NI}	—	350	—	μV_{P-P}	10 Hz to 10 MHz (Note 1)

Note 1: ENI is based on SPICE simulation.

2: Rise time t_R and t_{PLH} depend on the load (R_L and C_L). These specification are valid for the specified load only.

TEMPERATURE SPECIFICATIONS

Electrical Characteristics: Unless otherwise indicated: V_{DD} = +1.8v to +5.5v and V_{SS} = GND.								
Parameters	Symbol	Min.	Тур.	Max.	Units	Conditions		
Temperature Ranges								
Specified Temperature Range	T _A	-40		+125	°C			
Operating Temperature Range	T _A	-40		+125	°C			
Storage Temperature Range	T _A	-65		+150	°C			
Thermal Package Resistances								
Thermal Resistance, SC70-5	θ_{JA}	—	331	-	°C/W			
Thermal Resistance, SOT-23-5	θ_{JA}	—	201	-	°C/W			
Thermal Resistance, 8L-MSOP	θ_{JA}	_	211	_	°C/W			
Thermal Resistance, 8L-SOIC	θ_{JA}	—	149	-	°C/W			
Thermal Resistance, 14L-SOIC	θ_{JA}	_	91	—	°C/W			
Thermal Resistance, 14L-TSSOP	θ_{JA}	_	100	—	°C/W			

1.2 Test Circuit Configuration

This test circuit configuration is used to determine the AC and DC specifications.



FIGURE 1-1: AC and DC Test Circuit for the Open-Drain Output Comparators.

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (i.e., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, V_{DD} = +1.8V to +5.5V, V_{SS} = GND, T_A = +25°C, V_{IN} + = $V_{DD}/2$, V_{IN} - = GND, R_L = 20 k Ω to V_{PU} = V_{DD} , and C_L = 25 pF.









FIGURE 2-3: Input vs. Output Signal, No Phase Reversal.



FIGURE 2-4:

Input Hysteresis Voltage.



FIGURE 2-5: Input Hysteresis Voltage Drift – Linear Temp. Co. (TC1).



FIGURE 2-6: Input Hysteresis Voltage Drift – Quadratic Temp. Co. (TC2).

Note: Unless otherwise indicated, V_{DD} = +1.8V to +5.5V, V_{SS} = GND, T_A = +25°C, V_{IN} + = $V_{DD}/2$, V_{IN} - = GND, R_L = 20 k Ω to V_{PU} = V_{DD} , and C_L = 25 pF.



FIGURE 2-7: Temperature.



FIGURE 2-8: Input Offset Voltage vs. Common-mode Input Voltage.



FIGURE 2-9: Input Offset Voltage vs. Common-mode Input Voltage.



FIGURE 2-10: Input Hysteresis Voltage vs. Temperature.



FIGURE 2-11: Input Hysteresis Voltage vs. Common-mode Input Voltage.



FIGURE 2-12: Input Hysteresis Voltage vs. Common-mode Input Voltage.

Note: Unless otherwise indicated, V_{DD} = +1.8V to +5.5V, V_{SS} = GND, T_A = +25°C, V_{IN} + = $V_{DD}/2$, V_{IN^-} = GND, R_L = 20 k Ω to V_{PU} = V_{DD} , and C_L = 25 pF.



FIGURE 2-13: Input Offset Voltage vs. Supply Voltage vs. Temperature.





FIGURE 2-15: Quiescent Current vs. Common-mode Input Voltage.



FIGURE 2-16: Input Hysteresis Voltage vs. Supply Voltage vs. Temperature.



FIGURE 2-17: Quiescent Current vs. Supply Voltage vs. Temperature.



FIGURE 2-18: Quiescent Current vs. Common-mode Input Voltage.

Note: Unless otherwise indicated, V_{DD} = +1.8V to +5.5V, V_{SS} = GND, T_A = +25°C, V_{IN} + = $V_{DD}/2$, V_{IN} - = GND, R_L = 20 k Ω to V_{PU} = V_{DD} , and C_L = 25 pF.



FIGURE 2-19: Pull-up Voltage.





FIGURE 2-20: Quiescent Current vs. Toggle Frequency.



FIGURE 2-21: Output Headroom vs. Output Current.



FIGURE 2-22: Quiescent Current vs. Pull-up to Supply Voltage Difference.



FIGURE 2-23: Output Leakage Current vs. Pull-up Voltage.



FIGURE 2-24: Output Headroom vs. Output Current.

Note: Unless otherwise indicated, V_{DD} = +1.8V to +5.5V, V_{SS} = GND, T_A = +25°C, V_{IN} + = $V_{DD}/2$, V_{IN^-} = GND, R_L = 20 k Ω to V_{PU} = V_{DD} , and C_L = 25 pF.



FIGURE 2-25: High-to-Low Propagation Delays.



Over-Drive.



FIGURE 2-27: Propagation Delay vs. Supply Voltage.



FIGURE 2-28: High-to-Low Propagation Delays.



FIGURE 2-29: Propagation Delay vs. Temperature.



FIGURE 2-30: Short Circuit Current vs. Supply Voltage vs. Temperature.

Note: Unless otherwise indicated, V_{DD} = +1.8V to +5.5V, V_{SS} = GND, T_A = +25°C, V_{IN} + = $V_{DD}/2$, V_{IN} - = GND, R_L = 20 k Ω to V_{PU} = V_{DD} , and C_L = 25 pF.



FIGURE 2-31: Propagation Delay vs. Common-mode Input Voltage.



FIGURE 2-32: Propagation Delay vs. Capacitive Load.



FIGURE 2-33: Input Bias Current vs. Input Voltage vs. Temperature.



FIGURE 2-34: Propagation Delay vs. Common-mode Input Voltage.



FIGURE 2-35: Propagation Delay vs. Pull-up Resistor.



FIGURE 2-36:Propagation Delay vs.Pull-up Voltage.

Note: Unless otherwise indicated, V_{DD} = +1.8V to +5.5V, V_{SS} = GND, T_A = +25°C, V_{IN} + = $V_{DD}/2$, V_{IN} - = GND, R_L = 20 k Ω to V_{PU} = V_{DD} , and C_L = 25 pF.



FIGURE 2-37: Common-mode Rejection Ratio and Power Supply Rejection Ratio vs. Temperature.



FIGURE 2-38: Power Supply Rejection Ratio (PSRR).



FIGURE 2-39: Input Offset Current and Input Bias Current vs. Temperature.



Ratio (CMRR).

Common-mode Rejection

FIGURE 2-41: Common-mode Rejection Ratio (CMRR).

FIGURE 2-42: Input Offset Current and Input Bias Current vs. Common-mode Input Voltage vs. Temperature.

Note: Unless otherwise indicated, V_{DD} = +1.8V to +5.5V, V_{SS} = GND, T_A = +25°C, V_{IN} + = $V_{DD}/2$, V_{IN^-} = GND, R_L = 20 k Ω to V_{PU} = V_{DD} , and C_L = 25 pF.

FIGURE 2-43: Frequency.

3.0 PIN DESCRIPTIONS

Descriptions of the pins are listed in Table 3-1.

MCP6566	MCP6566R	MCP6566U	MCP6567	MCP6569		
SC70-5, SOT-23-5	SOT-23-5	SOT-23-5	MSOP, SOIC	SOIC, TSSOP	Symbol	Description
1	1	4	1	1	OUT, OUTA	Digital Output (comparator A)
4	4	3	2	2	V _{IN} —, V _{INA} —	Inverting Input (comparator A)
3	3	1	3	3	V _{IN} +, V _{INA} +	Non-inverting Input (comparator A)
5	2	5	8	4	V _{DD}	Positive Power Supply
_	—	-	5	5	V _{INB} +	Non-inverting Input (comparator B)
_	—	-	6	6	V _{INB} –	Inverting Input (comparator B)
_	—	_	7	7	OUTB	Digital Output (comparator B)
_	—	-	_	8	OUTC	Digital Output (comparator C)
_	—	-	_	9	V _{INC} -	Inverting Input (comparator C)
_	—	_	—	10	V _{INC} +	Non-inverting Input (comparator C)
2	5	2	4	11	V _{SS}	Negative Power Supply
_	_	_	_	12	V _{IND} +	Non-inverting Input (comparator D)
_	—	_	_	13	V _{IND} -	Inverting Input (comparator D)
_	_	_	_	14	OUTD	Digital Output (comparator D)

TABLE 3-1:PIN FUNCTION TABLE

3.1 Analog Inputs

The comparator non-inverting and inverting inputs are high-impedance CMOS inputs with low bias currents.

3.2 Digital Outputs

The comparator outputs are CMOS, open-drain digital outputs. They are designed to make level shifting and wired-OR easy to implement.

3.3 Power Supply (V_{SS} and V_{DD})

The positive power supply pin (V_{DD}) is 1.8V to 5.5V higher than the negative power supply pin (V_{SS}). For normal operation, the other pins are at voltages between V_{SS} and V_{DD}.

Typically, these parts are used in a single (positive) supply configuration. In this case, V_{SS} is connected to ground and V_{DD} is connected to the supply. V_{DD} will need a local bypass capacitor (typically 0.01 μ F to 0.1 μ F) within 2 mm of the V_{DD} pin. These can share a bulk capacitor with nearby analog parts (within 100 mm), but it is not required.

4.0 APPLICATIONS INFORMATION

The MCP6566/6R/6U/7/9 family of open-drain output comparators are fabricated on Microchip's state-of-the-art CMOS process. They are suitable for a wide range of high speed applications that require low-power consumption.

4.1 Comparator Inputs

4.1.1 NORMAL OPERATION

The input stage of this family of devices uses two different input stages in parallel. This configuration provides three regions of operation, one operates at low input voltages, one at high input voltages, and one at mid input voltage. With this topology, the input voltage range is 0.3V above V_{DD} and 0.3V below V_{SS} , while providing low offset voltage throughout the common mode range. The input offset voltage is measured at both V_{SS} - 0.3V and V_{DD} + 0.3V to ensure proper operation.

The MCP6566/6R/6U/7/9 family has an internally-set hysteresis V_{HYST}, which is small enough to maintain input offset accuracy and large enough to eliminate output chattering caused by the comparator's own input noise voltage $E_{\rm NI}$. Figure 4-1 depicts this behavior. Input offset voltage (V_{OS}) is the center (average) of the (input-referred) low-high and high-low trip points. Input hysteresis voltage (V_{HYST}) is the difference between the same trip points.

FIGURE 4-1: The MCP6566/6R/6U/7/9 comparators' internal hysteresis eliminates output chatter caused by input noise voltage.

4.1.2 INPUT VOLTAGE AND CURRENT LIMITS

The ESD protection on the inputs can be depicted as shown in Figure 4-2. This structure was chosen to protect the input transistors, and to minimize input bias current (I_B). The input ESD diodes clamp the inputs when they try to go more than one diode drop below V_{SS} . They also clamp any voltages that go too far above V_{DD} . The diodes' breakdown voltage is high enough to allow normal operation, but low enough to bypass ESD events within the specified limits.

In order to prevent damage and/or improper operation of these amplifiers, the circuits they are in must limit the currents (and voltages) at the V_{IN}+ and V_{IN}- pins (see Section 1.1 "Maximum Ratings †" at the beginning of Section 1.0 "Electrical Characteristics"). Figure 4-3 shows the recommended approach to protecting these inputs. The internal ESD diodes prevent the input pins (V_{IN}+ and V_{IN}-) from going too far below ground, and the resistors R₁ and R₂ limit the possible current drawn out of the input pin. Diodes D₁ and D₂ prevent the input pin (V_{IN}+ and V_{IN}-) from going too far above V_{DD}. When implemented as shown, resistors R₁ and R₂ also limit the current through D₁ and D₂.

FIGURE 4-3: Protecting the Analog Inputs.

It is also possible to connect the diodes to the left of the resistors R₁ and R₂. In this case, the currents through the diodes D₁ and D₂ need to be limited by some other mechanism. The resistor then serves as in-rush current limiter; the DC current into the input pins (V_{IN}+ and V_{IN}-) should be very small.

A significant amount of current can flow out of the inputs when the common mode voltage (V_{CM}) is below ground (V_{SS}); see Figure 4-3. Applications that are high-impedance may need to limit the usable voltage range.

4.1.3 PHASE REVERSAL

The MCP6566/6R/6U/7/9 comparator family uses CMOS transistors at the input. They are designed to prevent phase inversion when the input pins exceed the supply voltages. Figure 2-3 shows an input voltage exceeding both supplies with no resulting phase inversion.

4.2 Open-Drain Output

The open-drain output is designed to make level-shifting and wired-OR logic easy to implement. The output stage minimizes switching current (shoot-through current from supply-to-supply) when the output changes state. See Figures 2-15, 2-18, 2-35 and 2-36, for more information.

4.3 Externally Set Hysteresis

Greater flexibility in selecting hysteresis (or input trip points) is achieved by using external resistors. Hysteresis reduces output chattering when one input is slowly moving past the other. It also helps in systems in which it is best not to cycle between high and low states too frequently (e.g., air conditioner thermostatic control). Output chatter also increases the dynamic supply current.

4.3.1 NON-INVERTING CIRCUIT

Figure 4-4 shows a non-inverting circuit for single-supply applications using just two resistors. The resulting hysteresis diagram is shown in Figure 4-5.

FIGURE 4-4: Non-Inverting Circuit with Hysteresis for Single-Supply.

FIGURE 4-5: Hysteresis Diagram for the Non-Inverting Circuit.

The trip points for Figures 4-4 and 4-5 are:

EQUATION 4-1:

$$V_{TLH} = V_{REF} \left(I + \frac{R_I}{R_F} \right) - V_{OL} \left(\frac{R_I}{R_F} \right)$$
$$V_{THL} = V_{REF} \left(I + \frac{R_I}{R_F} \right) - V_{OH} \left(\frac{R_I}{R_F} \right)$$
Where:
$$V_{TLH} = \text{trip voltage from low-to-high}$$
$$V_{THL} = \text{trip voltage from high-to-low}$$

4.3.2 INVERTING CIRCUIT

Figure 4-6 shows an inverting circuit for single-supply using three resistors. The resulting hysteresis diagram is shown in Figure 4-7.

FIGURE 4-6: Inverting Circuit with Hysteresis.

FIGURE 4-7: Hysteresis Diagram for the Inverting Circuit.

In order to determine the trip voltages (V_{THL} and V_{TLH}) for the circuit shown in Figure 4-6, R₂ and R₃ can be simplified to the Thevenin equivalent circuit with respect to V_{DD}, as shown in Figure 4-8.

FIGURE 4-8:

Thevenin Equivalent Circuit.

Where:

$$R_{23} = \frac{R_2 R_3}{R_2 + R_3}$$
$$V_{23} = \frac{R_3}{R_2 + R_3} \times V_{DD}$$

Using this simplified circuit, the trip voltage can be calculated using the following equation:

EQUATION 4-2:

$$V_{THL} = V_{OH} \left(\frac{R_{23}}{R_{23} + R_F} \right) + V_{23} \left(\frac{R_F}{R_{23} + R_F} \right)$$
$$V_{TLH} = V_{OL} \left(\frac{R_{23}}{R_{23} + R_F} \right) + V_{23} \left(\frac{R_F}{R_{23} + R_F} \right)$$

Where:

 V_{TLH} = trip voltage from low-to-high V_{THL} = trip voltage from high-to-low

Figure 2-21 and Figure 2-24 can be used to determine typical values for V_{OH} and $V_{OL}.$

4.4 Bypass Capacitors

With this family of comparators, the power supply pin (V_{DD} for single supply) should have a local bypass capacitor (i.e., 0.01 μF to 0.1 μF) within 2 mm for good edge rate performance.

4.5 Capacitive Loads

Reasonable capacitive loads (e.g., logic gates) have little impact on propagation delay (see Figure 2-32). The supply current increases with increasing toggle frequency (Figure 2-20), especially with higher capacitive loads. The output slew rate and propagation delay performance will be reduced with higher capacitive loads.

4.6 PCB Surface Leakage

In applications where low input bias current is critical, PCB (Printed Circuit Board) surface leakage effects need to be considered. Surface leakage is caused by humidity, dust or other contamination on the board. Under low humidity conditions, a typical resistance between nearby traces is $10^{12}\Omega$. A 5V difference would cause 5 pA of current to flow. This is greater than the MCP6566/6R/6U/7/9 family's bias current at +25°C (1 pA, typical).

The easiest way to reduce surface leakage is to use a guard ring around sensitive pins (or traces). The guard ring is biased at the same voltage as the sensitive pin. An example of this type of layout is shown in Figure 4-9.

FIGURE 4-9: Example Guard Ring Layout for Inverting Circuit.

- 1. Inverting Configuration (Figures 4-6 and 4-9):
 - a) Connect the guard ring to the non-inverting input pin (V_{IN} +). This biases the guard ring to the same reference voltage as the comparator (e.g., $V_{DD}/2$ or ground).
 - b) Connect the inverting pin (V_{IN}-) to the input pad without touching the guard ring.
- 2. Non-inverting Configuration (Figure 4-4):
 - a) Connect the non-inverting pin (V_{IN} +) to the input pad without touching the guard ring.
 - b) Connect the guard ring to the inverting input pin (V_{IN} -).

4.7 PCB Layout Technique

When designing the PCB layout, it is critical to note that analog and digital signal traces are adequately separated to prevent signal coupling. If the comparator output trace is at close proximity to the input traces, then large output voltage changes from, V_{SS} to V_{DD} or visa versa, may couple to the inputs and cause the device output to oscillate. To prevent such oscillation, the output traces must be routed away from the input pins. The SC70-5 and SOT-23-5 are relatively immune because the output pin OUT (pin 1) is separated by the power pin V_{DD}/V_{SS} (pin 2) from the input pin +IN (as long as the analog and digital traces remain separated throughout the PCB). However, the pinouts for the dual and quad packages (SOIC, MSOP, TSSOP) have OUT and -IN pins (pin 1 and 2) close to each other. The recommended layout for these packages is shown in Figure 4-10.

4.8 Unused Comparators

An unused amplifier in a quad package (MCP6569) should be configured as shown in Figure 4-11. This circuit prevents the output from toggling and causing crosstalk. It uses the minimum number of components and draws minimal current (see Figure 2-15 and Figure 2-15).

FIGURE 4-11: Unused Comparators.

4.9 Typical Applications

4.9.1 PRECISE COMPARATOR

Some applications require higher DC precision. An easy way to solve this problem is to use an amplifier (such as the MCP6291) to gain-up the input signal before it reaches the comparator. Figure 4-12 shows an example of this approach.

FIGURE 4-12: Precise Inverting Comparator.

4.9.2 WINDOWED COMPARATOR

Figure 4-13 shows one approach to designing a windowed comparator. The AND gate produces a logic '1' when the input voltage is between V_{RB} and V_{RT} (where V_{RT} > V_{RB}).

FIGURE 4-13:

Windowed Comparator.

4.9.3 BISTABLE MULTIVIBRATOR

A simple bistable multivibrator design is shown in Figure 4-14. V_{REF} needs to be between the power supplies (V_{SS} = GND and V_{DD}) to achieve oscillation. The output duty cycle changes with V_{REF}.

FIGURE 4-14: Bistable Multivibrator.

6.0 PACKAGING INFORMATION

6.1 Package Marking Information

5-Lead SOT-23 (MCP6566, MCP6566R)

8-Lead MSOP (MCP6567)

XXXXXX

YWWNNN

 \mathbf{v}

Device	Code			
MCP6566T	JYNN			
MCP6566RT	JZNN			
MCP6566UT	WLNN			
Neter Anglias to 5 Least OOT 00				

Note: Applies to 5-Lead SOT-23.

Example:

Example:

Legend	: XXX Y YY WW NNN @3 *	Customer-specific information Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC designator for Matte Tin (Sn) This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.
Note:	In the ever be carried characters	nt the full Microchip part number cannot be marked on one line, it will d over to the next line, thus limiting the number of available for customer-specific information.

8-Lead SOIC (150 mil) **(MCP6567)**

0

Package Marking Information (Continued)

14-Lead TSSOP (MCP6569)

Example:

5-Lead Plastic Small Outline Transistor (LT) [SC70]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

	Units	MILLIMETERS		
Dimensior	n Limits	MIN	NOM	MAX
Number of Pins	Ν		5	
Pitch	е		0.65 BSC	
Overall Height	А	0.80	-	1.10
Molded Package Thickness	A2	0.80	-	1.00
Standoff	A1	0.00	-	0.10
Overall Width	Е	1.80	2.10	2.40
Molded Package Width	E1	1.15	1.25	1.35
Overall Length	D	1.80	2.00	2.25
Foot Length	L	0.10	0.20	0.46
Lead Thickness	С	0.08	_	0.26
Lead Width	b	0.15	_	0.40

Notes:

1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.

2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-061B

5-Lead Plastic Small Outline Transistor (LT) [SC70]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

RECOMMENDED LAND PATTERN

	Units	N	S	
Dimension	Dimension Limits		NOM	MAX
Contact Pitch	E		0.65 BSC	
Contact Pad Spacing	С		2.20	
Contact Pad Width	X			0.45
Contact Pad Length	Y			0.95
Distance Between Pads	G	1.25		
Distance Between Pads	Gx	0.20		

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2061A

5-Lead Plastic Small Outline Transistor (OT) [SOT-23]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

L1 -

	Units			MILLIMETERS			
	Dimension Limits	MIN	NOM	MAX			
Number of Pins	N		5				
Lead Pitch	е		0.95 BSC				
Outside Lead Pitch	e1		1.90 BSC				
Overall Height	А	0.90	-	1.45			
Molded Package Thickness	A2	0.89	-	1.30			
Standoff	A1	0.00	-	0.15			
Overall Width	E	2.20	-	3.20			
Molded Package Width	E1	1.30	-	1.80			
Overall Length	D	2.70	-	3.10			
Foot Length	L	0.10	-	0.60			
Footprint	L1	0.35	-	0.80			
Foot Angle	ф	0°	-	30°			
Lead Thickness	С	0.08	-	0.26			
Lead Width	b	0.20	_	0.51			

Notes:

- 1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
- 2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-091B

5-Lead Plastic Small Outline Transistor (OT) [SOT-23]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

	MILLIMETERS				
Dimension	MIN	NOM	MAX		
Contact Pitch	ontact Pitch E		0.95 BSC		
Contact Pad Spacing	С		2.80		
Contact Pad Width (X5)	X			0.60	
Contact Pad Length (X5)	Y			1.10	
Distance Between Pads	G	1.70			
Distance Between Pads	GX	0.35			
Overall Width	Z			3.90	

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2091A

8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

Microchip Technology Drawing C04-111C Sheet 1 of 2

8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

DETAIL C

	MILLIMETERS					
Dimensior	Dimension Limits		NOM	MAX		
Number of Pins	N		8			
Pitch	е		0.65 BSC			
Overall Height	A	-	-	1.10		
Molded Package Thickness	A2	0.75	0.85	0.95		
Standoff	A1	0.00	-	0.15		
Overall Width	E	4.90 BSC				
Molded Package Width	E1	3.00 BSC				
Overall Length	D	3.00 BSC				
Foot Length	L	0.40	0.60	0.80		
Footprint	L1	0.95 REF				
Foot Angle	φ	0°	-	8°		
Lead Thickness	С	0.08	-	0.23		
Lead Width	b	0.22	-	0.40		

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or

- protrusions shall not exceed 0.15mm per side.
- 3. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-111C Sheet 2 of 2

8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

RECOMMENDED LAND PATTERN

	Units		MILLIMETERS			
Dimension Limits		MIN	NOM	MAX		
Contact Pitch	E	0.65 BSC				
Contact Pad Spacing	С		4.40			
Overall Width	Z			5.85		
Contact Pad Width (X8)	X1			0.45		
Contact Pad Length (X8)	Y1			1.45		
Distance Between Pads	G1	2.95				
Distance Between Pads	GX	0.20				

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2111A

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

Microchip Technology Drawing No. C04-057C Sheet 1 of 2

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

	Units	MILLIMETERS			
Dimension Limits		MIN	NOM	MAX	
Number of Pins	Ν		8		
Pitch	е		1.27 BSC		
Overall Height	Α	-	-	1.75	
Molded Package Thickness	A2	1.25	-	-	
Standoff §	A1	0.10	-	0.25	
Overall Width	E	6.00 BSC			
Molded Package Width	E1	3.90 BSC			
Overall Length	D	4.90 BSC			
Chamfer (Optional)	h	0.25 - 0.50			
Foot Length	L	0.40	-	1.27	
Footprint	L1	1.04 REF			
Foot Angle	φ	0°	-	8°	
Lead Thickness	С	0.17	-	0.25	
Lead Width	b	0.31	-	0.51	
Mold Draft Angle Top	α	5°	-	15°	
Mold Draft Angle Bottom	β	5°	_	15°	

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. § Significant Characteristic

3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.

4. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-057C Sheet 2 of 2

8-Lead Plastic Small Outline (SN) – Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

RECOMMENDED LAND PATTERN

	Units	MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Contact Pitch	E		1.27 BSC	
Contact Pad Spacing	С		5.40	
Contact Pad Width (X8)	X1			0.60
Contact Pad Length (X8)	Y1			1.55

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2057A

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

VIEW A-A

Microchip Technology Drawing No. C04-065C Sheet 1 of 2

14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

	Units	MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Number of Pins	Ν	14		
Pitch	е	1.27 BSC		
Overall Height	А	- 1.75		
Molded Package Thickness	A2	1.25	-	-
Standoff §	A1	0.10	-	0.25
Overall Width	E	6.00 BSC		
Molded Package Width	E1	3.90 BSC		
Overall Length	D	8.65 BSC		
Chamfer (Optional)	h	0.25 - 0.50		
Foot Length	L	0.40	-	1.27
Footprint	L1	1.04 REF		
Lead Angle	Θ	0°	-	-
Foot Angle	φ	0° - 8°		
Lead Thickness	С	0.10 - 0.25		
Lead Width	b	0.31	-	0.51
Mold Draft Angle Top	α	5°	-	15°
Mold Draft Angle Bottom	β	5°	-	15°

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. § Significant Characteristic

- Dimension D does not include mold flash, protrusions or gate burrs, which shall not exceed 0.15 mm per end. Dimension E1 does not include interlead flash or protrusion, which shall not exceed 0.25 mm per side.
- Dimensioning and tolerancing per ASME Y14.5M
 BSC: Basic Dimension. Theoretically exact value shown without tolerances.
 REF: Reference Dimension, usually without tolerance, for information purposes only.
- 5. Datums A & B to be determined at Datum H.

Microchip Technology Drawing No. C04-065C Sheet 2 of 2

14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

RECOMMENDED LAND PATTERN

	Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX	
Contact Pitch	E		1.27 BSC		
Contact Pad Spacing	С		5.40		
Contact Pad Width	X			0.60	
Contact Pad Length	Y			1.50	
Distance Between Pads	Gx	0.67			
Distance Between Pads	G	3.90			

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2065A

14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

Microchip Technology Drawing C04-087C Sheet 1 of 2

14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

	Units	s MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Number of Pins	N	14		
Pitch	е	0.65 BSC		
Overall Height	A	1.20		
Molded Package Thickness	A2	0.80	1.00	1.05
Standoff	A1	0.05	-	0.15
Overall Width	E	6.40 BSC		
Molded Package Width	E1	4.30	4.40	4.50
Molded Package Length	D	4.90	5.00	5.10
Foot Length	L	0.45	0.60	0.75
Footprint	(L1)	1.00 REF		
Foot Angle	φ	0°	-	8°
Lead Thickness	c	0.09	-	0.20
Lead Width	b	0.19	-	0.30

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

- 2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 3. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-087C Sheet 2 of 2

14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

RECOMMENDED LAND PATTERN

Units		MILLIMETERS			
Dimension Limits		MIN	NOM	MAX	
Contact Pitch	E		0.65 BSC		
Contact Pad Spacing	C1		5.90		
Contact Pad Width (X14)	X1			0.45	
Contact Pad Length (X14)	Y1			1.45	
Distance Between Pads	G	0.20			

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2087A

APPENDIX A: REVISION HISTORY

Revision E (November 2014)

The following is the list of modifications:

- 1. Added SPICE Macro Model in the Related Device features section.
- 2. Updated Temperature Specifications table.
- 3. Corrected pin table in Section 3.0, Pin Descriptions.
- 4. Added new Section 5.4, SPICE Macro Model.

Revision D (February 2013)

The following is the list of modifications:

1. Added the Analog Input (V_{IN}) parameter in Section 1.0 "Electrical Characteristics".

Revision C (February 2011)

The following is the list of modifications:

1. Replaced the MCP5468 package name with the correct MCP6567 package name on page 1 and in Table 3-1.

Revision B (August 2009)

The following is the list of modifications:

- 1. Added MCP6566U throughout the document.
- 2. Updated package outline drawings.

Revision A (March 2009)

• Original Release of this Document.

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

<u>PART NO. – X</u>	<u>/xx</u>	Exa	amples:	
Device Temperature Pa Range	ckage	a)	MCP6566T-E/LT:	Tape and Reel, Extended Temperature, 5LD SC70 package.
Device: MCP6566T:	Single Comparator (Tape and Reel) (SC70, SOT-23)	b)	MCP6566T-E/OT:	Tape and Reel Extended Temperature, 5LD SOT-23 package.
MCP6566UT: MCP6567	(SOT-23 only) Single Comparator (Tape and Reel) (SOT-23 only) Dual Comparator	a)	MCP6566RT-E/OT:	Tape and Reel Extended Temperature, 5LD SOT-23 package.
MCP6567T: MCP6569: MCP6569T:	Dual Comparator (Tape and Reel) Quad Comparator Quad Comparator (Tape and Reel)	a)	MCP6566UT-E/OT:	Tape and Reel Extended Temperature, 5LD SOT-23 package.
Temperature $E = -40^{\circ}C \text{ to}$ Range:	o +125°C	a)	MCP6567-E/MS:	Extended Temperature 8LD MSOP package.
		b)	MCP6567-E/SN:	Extended Temperature 8LD SOIC package.
Package: LI = Plastic MS = Plastic SN = Plastic ST = Plastic SL = Plastic	Small Outline Transistor (SC70), 5-lead Small Outline Transistor (SOT-23), 5-lead Micro Small Outline Transistor, 8-lead Small Outline Transistor, 8-lead Thin Shrink Small Outline Transistor, 14-lead Small Outline Transistor, 14-lead	a) b)	MCP6569T-E/SL: MCP6569T-E/ST:	Tape and Reel Extended Temperature 14LD SOIC package. Tape and Reel Extended Temperature 14LD TSSOP package.